2N2907A

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS		•		
Collector – Emitter Breakdown Voltage (I _C = –10 mAdc)	V _(BR) CEO	-60	_	Vdc
Collector – Emitter Cutoff Current (V _{CE} = -50 Vdc)	ICES	-	-50	nAdc
Collector–Base Cutoff Current $(V_{CB} = -50 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -60 \text{ Vdc}, I_E = 0)$	Ісво	- -	-10 -10	nAdc μAdc
Emitter-Base Cutoff Current (V _{EB} = -4.0 Vdc) (V _{EB} = -5.0 Vdc)	I _{EBO}	- -	-50 -10	nAdc μAdc
ON CHARACTERISTICS (Note 1)				
DC Current Gain $ \begin{array}{l} (I_C = -0.1 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -1.0 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -10 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -150 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ (I_C = -500 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ \end{array} $	h _{FE}	75 100 100 100 50	- 450 - 300 -	_
Collector – Emitter Saturation Voltage (I_C = -150 mAdc, I_B = -15 mAdc) (I_C = -500 mAdc, I_B = -50 mAdc)	V _{CE} (sat)	- -	-0.4 -1.6	Vdc
Base – Emitter Saturation Voltage (I_C = -150 mAdc, I_B = -15 mAdc) (I_C = -500 mAdc, I_B = -50 mAdc)	V _{BE(sat)}	-0.6 -	-1.3 -2.6	Vdc
SMALL-SIGNAL CHARACTERISTICS		•		
Magnitude of Small–Signal Current Gain (I _C = –20 mAdc, V _{CE} = –20 Vdc, f = 100 MHz)	h _{fe}	2.0	_	_
Small–Signal Current Gain (I _C = -1.0 mAdc, V _{CE} = -10 Vdc, f = 1 kHz)	h _{fe}	100	_	_
Output Capacitance $(V_{CB} = -10 \text{ Vdc}, I_E = 0, 100 \text{ kHz} \le f \le 1.0 \text{ MHz})$	C _{obo}	-	8.0	pF
Input Capacitance ($V_{EB} = -2.0 \text{ Vdc}$, $I_C = 0$, 100 kHz \leq f \leq 1.0 MHz)	C _{ibo}	-	30	pF
SWITCHING CHARACTERISTICS	1			
Turn-On Time (Reference Figure in MIL-PRF-19500/291)	t _{on}	-	45	ns
Turn-Off Time (Reference Figure in MIL-PRF-19500/291)	t _{off}	-	300	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = $300 \,\mu$ s, Duty Cycle $\leq 2.0\%$.

2N2907A

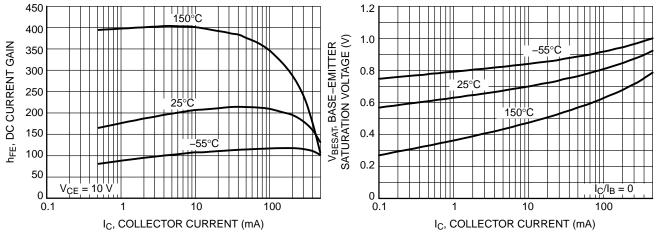


Figure 1. DC Current Gain Figure 2. Base-Emitter Saturation Voltage

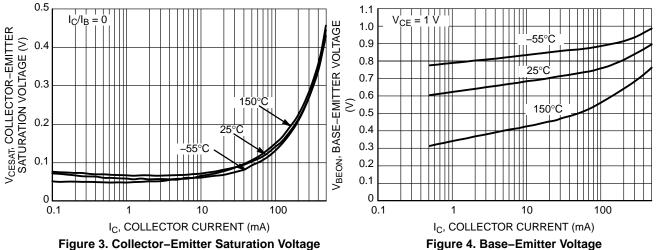


Figure 3. Collector-Emitter Saturation Voltage

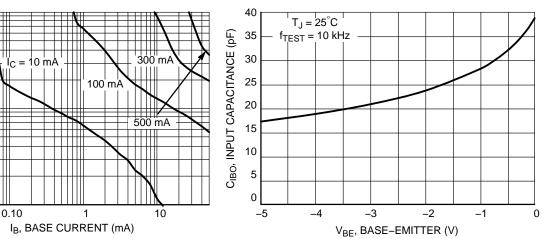


Figure 5. Collector Saturation Region

Figure 6. Input Capacitance

1.0

0.01 0.01

V_{CESAT}, COLLECTOR-EMITTER SATURATION VOLTAGE (V)

2N2907A

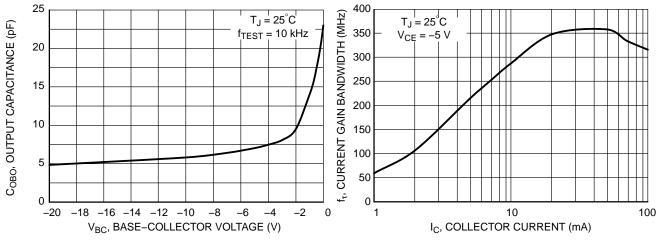


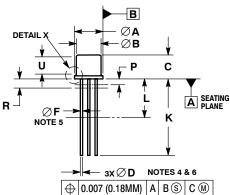
Figure 7. Output Capacitance

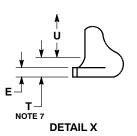
Figure 8. Current Gain Bandwidth Product



TO-18 CASE 206AA **ISSUE A**

DATE 21 AUG 2012







LEAD IDENTIFICATION

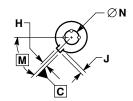
DETAIL

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: INCHES.

- DIMENSION J MEASURED FROM DIAMETER A TO EDGE.
 LEAD TRUE POSITION TO BE DETERMINED AT THE GUAGE PLANE DEFINED BY DIMENSION R.
 DIMENSION F APPLIES BETWEEN DIMENSION P AND L.
- DIMENSION D APPLIES BETWEEN DIMENSION L AND K.
- BODY CONTOUR OPTIONAL WITHIN ZONE DEFINED BY DIMENSIONS A, B, AND T.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	5.31	5.84	0.209	0.230
В	4.52	4.95	0.178	0.195
С	4.32	5.33	0.170	0.210
D	0.41	0.53	0.016	0.021
Е		0.76		0.030
F	0.41	0.48	0.016	0.019
Н	0.91	1.17	0.036	0.046
J	0.71	1.22	0.028	0.048
K	12.70	19.05	0.500	0.750
L	6.35		0.250	
M	45°BSC		45 °BSC	
N	2.54 BSC		0.100 BSC	
P		1.27		0.050
R	1.37 BSC		0.054 BSC	
T		0.76		0.030
U	2.54		0.100	



STYLE 1:	
PIN 1.	EMITTER
2.	BASE
3.	COLLECTOR

STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE & CASE

STYLE 7: PIN 1. ANODE 2. BASE 3. CATHODE

STYLE 10: PIN 1. BASE 2. EMITTER 3. BASE

STYLE 2: PIN 1. SOURCE, SUBSTRATE & CASE 2. GATE

3. DRAIN

STYLE 5: PIN 1. EMITTER 2. BASE 1 3 BASE 2

STYLE 8: PIN 1. GATE 2. ANODE 1 3. ANODE 2

STYLE 11:
PIN 1. DRAIN
2. GATE
3. SOURCE, SUBSTRATE

STYLE 3: PIN 1. SOURCE

2. DRAIN 3. GATE

STYLE 6: PIN 1. CATHODE 2. GATE 3. ANODE

STYLE 9: PIN 1. ANODE 2 2. ANODE 1 3. GATE

(CONNECTED TO CASE)

STYLE 12: PIN 1. SOURCE 2. GATE 3. DRAIN (CASE)

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DESCRIPTION:	TO-18 3-LEAD		PAGE 1 OF 1

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